





V. Vaganov 09/596,837 Examiner. 06/19/2000 Attorney's Docket No.: SS-714-01 METHOD FOR FABRICATING MICROSTRUCTURES WITH DEEP ANISOTROPIC ETCHING OF THICK SILICON WAFERSOLOGY Date of this Paper: 1000 IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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RESPONSE TO RESTRICTION REQUIREMENT

In response to the Patent Office Action mailed 11/18/2002, kindly enter the following:

Applicant respectfully traverses the merits of the request. However, applicant elects the isotropic dry etching step claims as indicated in the Office Action (i.e. claims 26, 29-30, 33-34, 48, 51-52, 55, 85, 88, 105, 108 and 115) in the event that no generic claims are finally found allowable.

Respectfully submitted

Dated: 12/12/2002

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I besidy certify that this correspondence is being described with the limited States Postal Service de first class mail to an expelope addressed to Commissioner of Petosta and Tradesserks, Westmore at 12/12/2002

Orte of Deposit THOMAS E. SCHATZEL

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Date